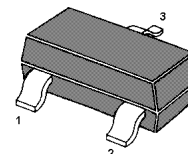



2SC1623
TRANSISTOR (NPN)
FEATURE

 High DC current gain : $h_{FE}=200(\text{Typ})$ $V_{CE}=6V$, $I_C=1mA$

 High voltage: $V_{CEO}=50V$
SOT-23


1. BASE
2. EMITTER
3. COLLECTOR

MARKING: L6
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	100	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA$, $I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60V$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6V$, $I_C=1mA$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA$, $I_B=10mA$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA$, $I_B=10mA$			1	V
Transition frequency	f_T	$V_{CE}=6V$, $I_C=10mA$		250		MHz

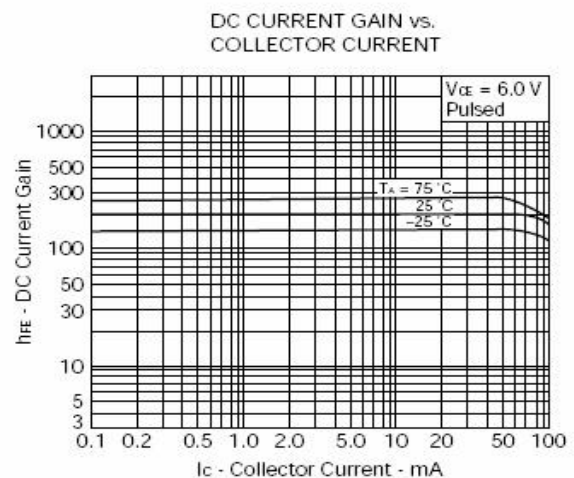
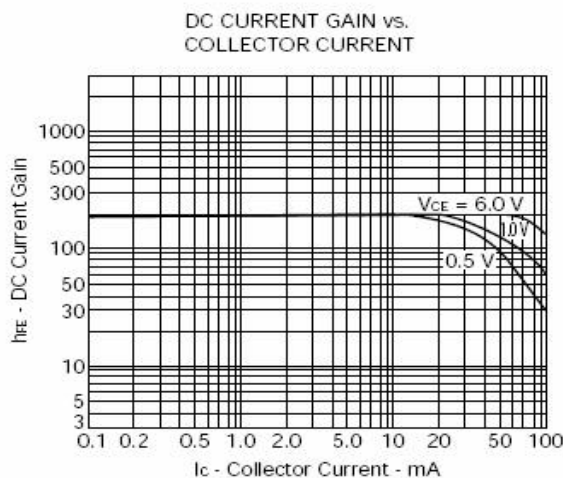
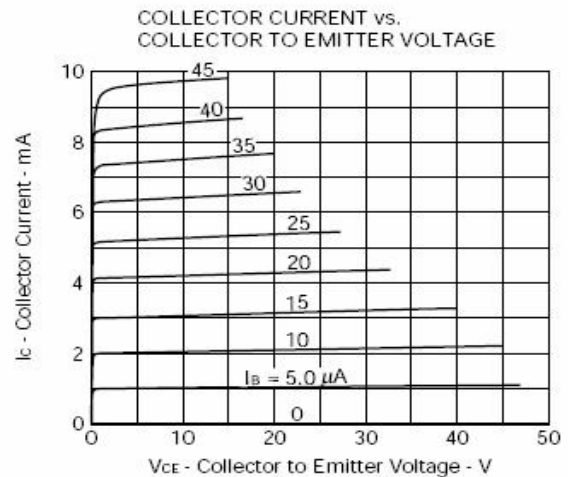
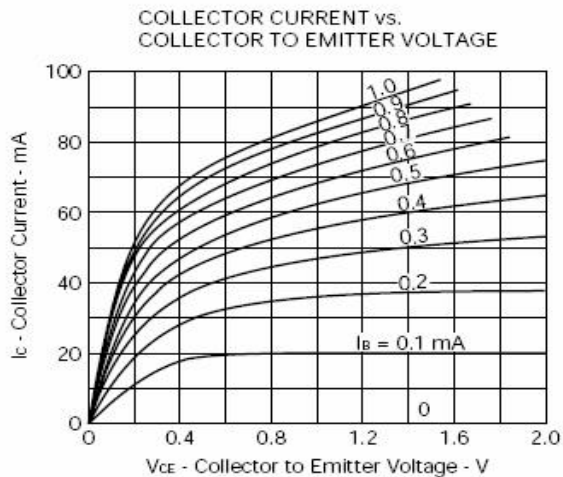
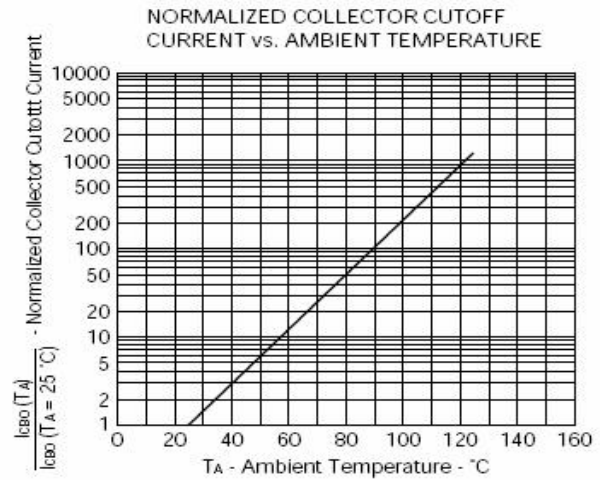
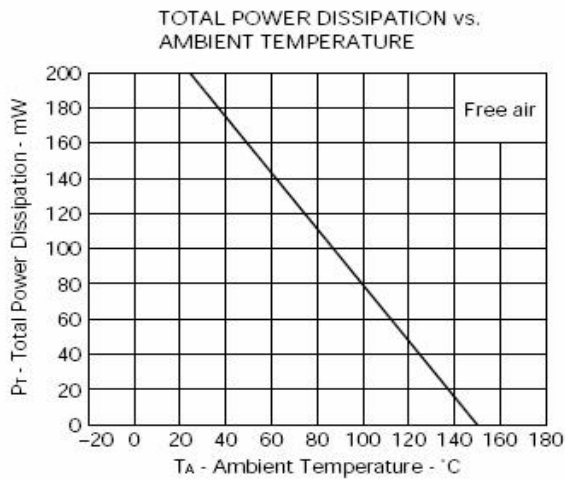


RoHS
COMPLIANT



Typical Characteristics

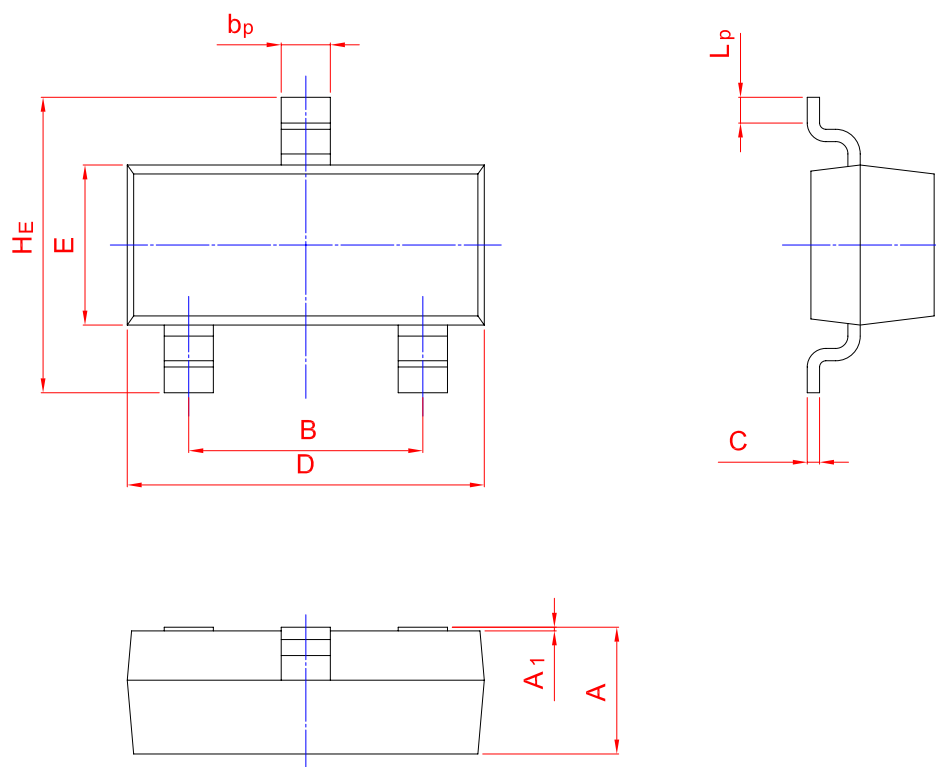
2SC1623



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20